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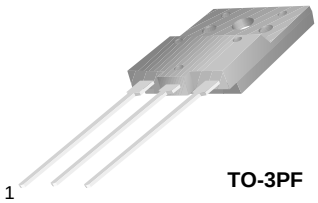
Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

October 2009

FJAF4210
PNP Epitaxial Silicon Transistor

Features

- Audio Power Amplifier
- High Current Capability : I_C= -10A
- High Power Dissipation
- Wide S.O.A
- Complement to FJAF4310



TO-3PF

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings* T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-140	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current (DC)	-10	A
I_B	Base Current (DC)	-1.5	A
P_C	Collector Dissipation (T_C=25°C)	80	W
$R_{\theta JC}$	Junction to Case	1.33	°C/W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C=-5mA, I_E=0	-200			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C=-50mA, R_{BE}=∞	-140			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E=-5mA, I_C=0	-6			V
I_{CBO}	Collector Cut-off Current	V_{CB}=-200V, I_E=0			-10	μA
I_{EBO}	Emitter Cut-off Current	V_{EB}=-6V, I_C=0			-10	μA
h_{FE}	* DC Current Gain	V_{CE}=-4V, I_C=-3A	50		180	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C=-5A, I_B=-0.5A			-0.5	V
C_{ob}	Output Capacitance	V_{CB}=-10V, f=1MHz		400		pF
f_T	Current Gain Bandwidth Product	V_{CE}=-5V, I_C=-1A		30		MHz

***** Pulse Test : PW=20μs

h_{FE} Classification

Classification	R	O	Y
h_{FE}	50 ~ 100	70 ~ 140	90 ~ 180

Typical Perpormance Characteristics

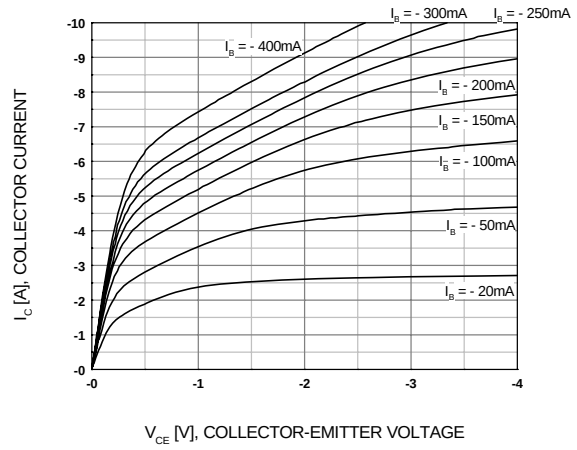


Figure 1. Static Characterstic

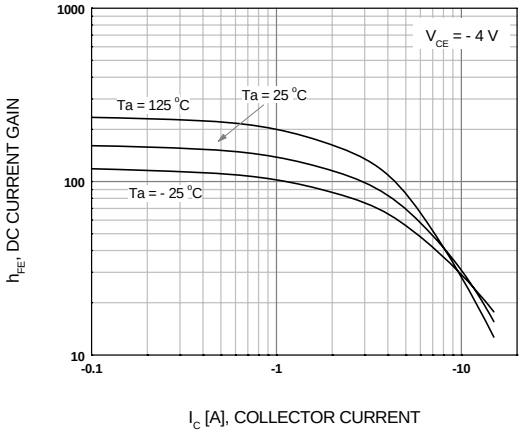


Figure 2. DC current Gain

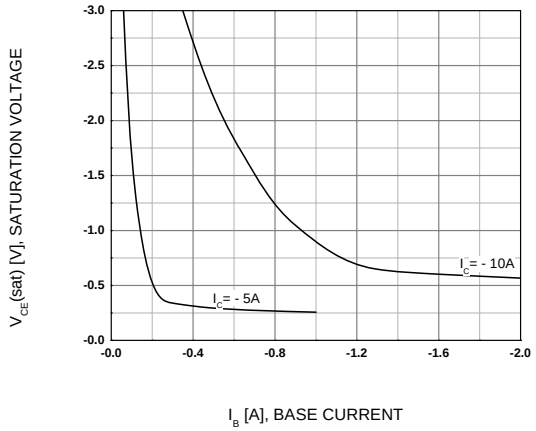


Figure 3. V_{CE}(sat) vs. I_B Characteristics

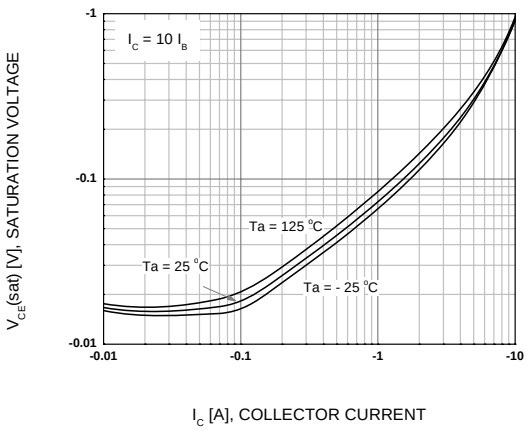


Figure 4. Collector-Emitter Saturation Voltage

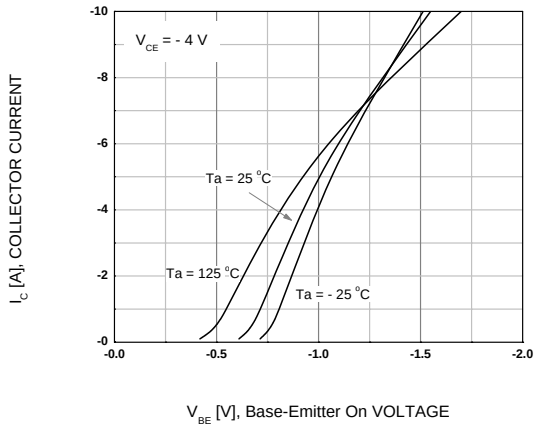


Figure 5. Base-Emitter On Voltage

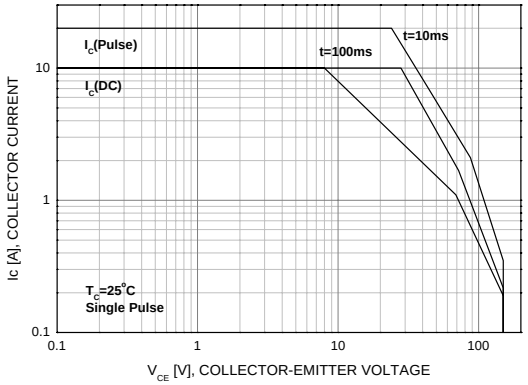


Figure 6. Forward Bias Safe Operating Area

Typical Perpormance Characteristics (Continued)

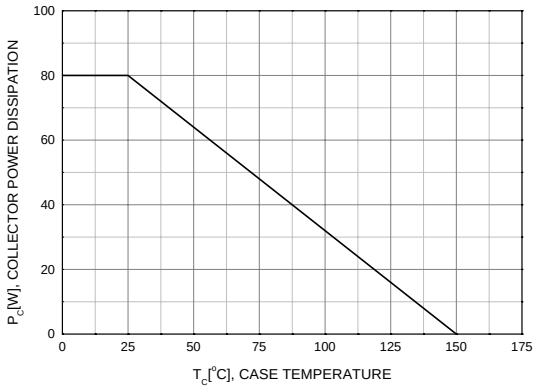
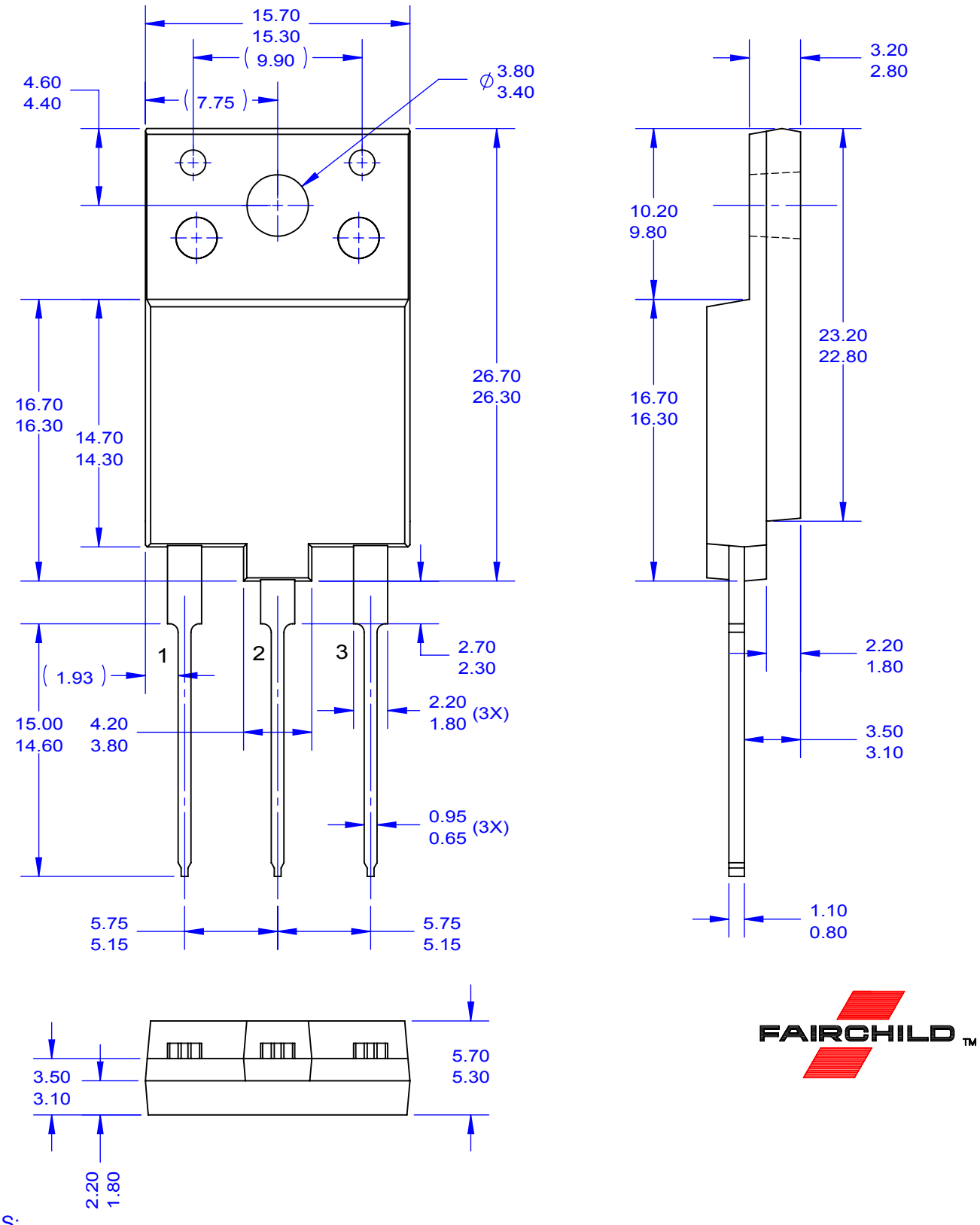


Figure 7. Power Derating



NOTES:

A. THIS PACKAGE CONFORMS TO SC94
JEITA PACKAGING STANDARD.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS ARE EXCLUSIVE OF BURRS,
MOLD FLASH AND TIE BAR PROTRUSIONS.
D. PIN 2 CONNECTS TO DAP.
E. DRAWING FILE NAME: TO3PFA03REV2

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